

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

I. LISTING OF CLAIMS:

1. to 8. (Canceled).

9. (currently amended): A method for fabricating a nitride-based semiconductor light emitting device, including:

forming at least a first nitride-based semiconductor layer; and

forming a current narrowing structure on said at least a first nitride-based semiconductor layer, comprising:

forming, on ~~an underlying~~ said at least a first nitride-based semiconductor layer, a mask of a material including nitrogen as a constituent element, and then

selectively crystal-growing at least ~~[[one]]~~ a second nitride-based semiconductor layer in an opening of said mask, ~~so as to form at least one of a current narrowing structure and a structure confining a light in a horizontal direction in parallel to a~~
~~substrate.~~

10. (Original): A method for fabricating a nitride-based semiconductor light emitting device, claimed in Claim 9 wherein said material including nitrogen as the constituent element is silicon nitride.

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11. (Original): A method for fabricating a nitride-based semiconductor light emitting device, claimed in Claim 10 wherein the coverage of said mask is not greater than 50%.

12. (Currently amended): A method for fabricating a nitride-based semiconductor light emitting device, claimed in Claim 9, ~~including~~ the step of forming at least a first nitride-based semiconductor layer comprising:

forming on ~~[[the]]~~ a substrate ~~at least one layer including~~ at least a nitride-based semiconductor layer of a first conductivity type,

forming at least one nitride-based semiconductor layer including at least an active layer, and

forming at least one nitride-based semiconductor layer ~~including at least a semiconductor layer~~ of a second conductivity type,

wherein the opening in said mask is stripe-shaped, and the step of forming a mask having a stripe shaped opening by a material including nitrogen as a constituent element, and the step of forming, in the opening of said mask, said at least [[one]] a second nitride-based semiconductor layer including at least includes a nitride-based semiconductor layer of the second conductivity type.

13. (Original): A method for fabricating a nitride-based semiconductor light emitting device, claimed in Claim 12 wherein said material including nitrogen as the constituent element is silicon nitride.

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14. (Original): A method for fabricating a nitride-based semiconductor light emitting device, claimed in Claim 13 wherein the coverage of said mask is not greater than 50%.

15.- 26. (Canceled).

27. (New): A method for fabricating a nitride-based semiconductor light emitting device, including:

forming at least a first nitride-based semiconductor layer; and

forming a structure on said at least a first nitride-based semiconductor layer, said structure confining light of said nitride-based semiconductor light emitting device in a horizontal direction in parallel to a substrate, comprising:

forming, on said at least a first nitride-based semiconductor layer, a mask of a material including nitrogen as a constituent element, and then

selectively crystal-growing at least a second nitride-based semiconductor layer in an opening of said mask.

28. (New): A method for fabricating a nitride-based semiconductor light emitting device, claimed in Claim 27 wherein said material including nitrogen as the constituent element is silicon nitride.

29. (New): A method for fabricating a nitride-based semiconductor light emitting device, claimed in Claim 27 wherein the coverage of said mask is not greater than 50%.

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30. (New): A method for fabricating a nitride-based semiconductor light emitting device, claimed in Claim 27, the step of forming at least a first nitride-based semiconductor layer comprising:

forming on the substrate at least one layer including at least a nitride-based semiconductor layer of a first conductivity type,

forming at least one nitride-based semiconductor layer including at least an active layer, and

forming at least one nitride-based semiconductor layer including a semiconductor layer of a second conductivity type,

wherein the opening in said mask is stripe-shaped, and said at least a second nitride-based semiconductor layer includes a nitride-based semiconductor layer of the second conductivity type.

31. (New): A method for fabricating a nitride-based semiconductor light emitting device, claimed in Claim 30 wherein said material including nitrogen as the constituent element is silicon nitride.

32. (New): A method for fabricating a nitride-based semiconductor light emitting device, claimed in Claim 31 wherein the coverage of said mask is not greater than 50%.